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## (54) FILM FORMING METHOD OF OXIDE SUPERCONDUCTOR

### (57)Abstract:

PURPOSE: To improve the smoothness of a film and improve crystallizability in the atomic layer epitaxy film forming.

CONSTITUTION: In the film forming method of the oxide superconductor forming the atomic layer epitaxy film of the oxide superconductor consisting of the compd. containing more than three component metal element, the process in which plural metal elements consisting of one part of an unit lattice is laminated simultaneously as one unit is included. In the film forming method of  $\text{RBa}_2\text{Cu}_3\text{O}_{7-\delta}$  (R is either one among Y, La, Pr, Nd, Sm, Eu, Gd, Dy, Ho, Er and Yb), the simultaneously laminating process of Cu, R and Cu as a subunit in order of Ba/Cu, R and Cu/Ba/Cu is included.

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